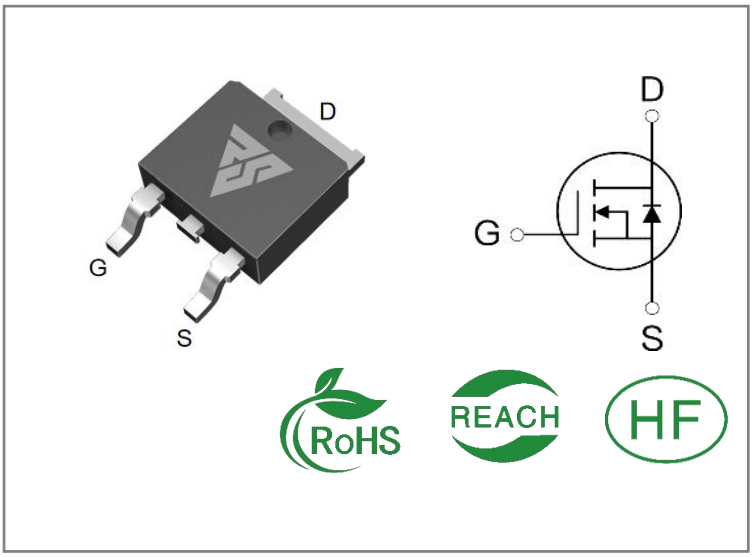
ID	R_{DS}(ON)(Typ)	VDSS
70A	4.5mΩ	40V



Applications:

- Load Switch
- PWM Applications
- Power Managment

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS40N70D	T0-252	RS40N70D	Tape&reel	2500 PCS

Absolute Maximun Ratings Tc= 2 5℃ unless otherwise specified

Symbol	Parameter	RS40N70D	Units
VDSS	Drain-to-Source Voltage	40	V
ID	Continuous Drain Current TC=25℃	70	A
ID	Continuous Drain Current TC=100℃	44	
IDM	Pulsed Drain Current (Note*1)	280	
PD	Power Dissipation	60	W
VGS	Gate- to- Source Voltage	±20	V
EAS	Single Pulse Avalanche Engergy L = 0.5mH, VDD = 20V, RG = 25 Ω,TC=25℃	120	mJ
TL TPKG	Maximum Temperature for Soldering	300 260	℃
	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds		
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS40N70D	Units	Test Conditions
RθJC	Junction-to-Case	2.1	℃/ W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 ℃
RθJA	Junction-to- Ambient	34		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	40	--	--	V	VGS=0V,ID=250μA
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	VDS=40V,VGS=0V
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	VGS=20V ,VDS=0V
	Gate- to- Source Reverse Leakage	--	--	-100		VGS=-20V ,VDS=0 V

ON Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	4.5	5.8	mΩ	VGS=10V,ID=30A
		--	6.5	8.5	mΩ	VGS=4.5V,ID=20A
VGS(TH)	Gate Threshold Voltage	1.3	1.8	2.3	V	VGS=VDS,ID=250μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	11	--	nS	VDS=20V ID=30A RG=3Ω
trise	Rise Time	--	32	--		
td(OFF)	Turn- OFF Delay Time	--	52	--		
tfall	Fall Time	--	13	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	3010	--	pF	VGS=0V VDS=20V f=1.0MHz
Coss	Output Capacitance	--	212	--		
Crss	Reverse Transfer Capacitance	--	178	--		
Qg	Total Gate Charge	--	58	--	nC	VDS=20V ID=30A VGS=10V
Qgs	Gate- to- Source Charge	--	12	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	12	--		

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	70	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	280	A	
VSD	Diode Forward Voltage	--	--	1.2	V	IS=30A,VGS=0V
trr	Reverse Recovery Time	--	13	--	nS	VGS=0V IS=20A di/dt=100A/μs
Qrr	Reverse Recovery Charge	--	7	--	nC	

Notes:

* 1. Repetitive rating, pulse width limited by maximum junction temperature.
* 2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 0.5%

Typical Feature Curve

Figure 1: Output Characteristics

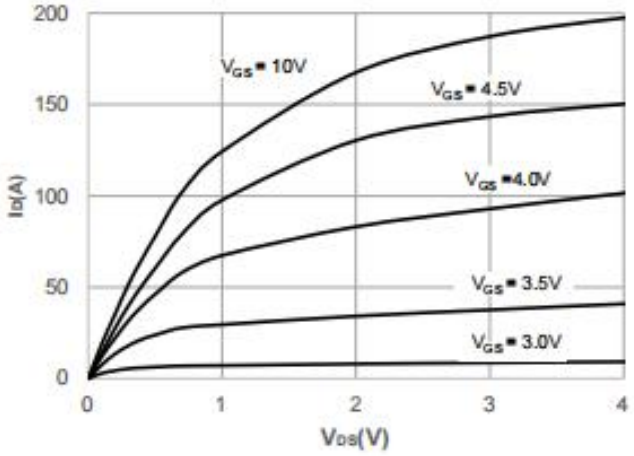


Figure 2: Typical Transfer Characteristics

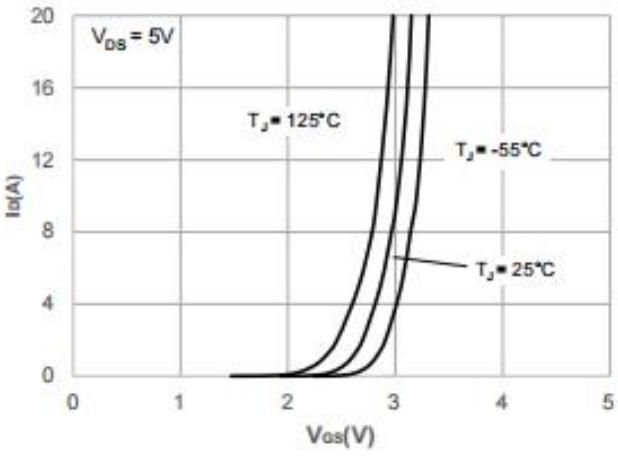


Figure 3: On-resistance vs. Drain Current

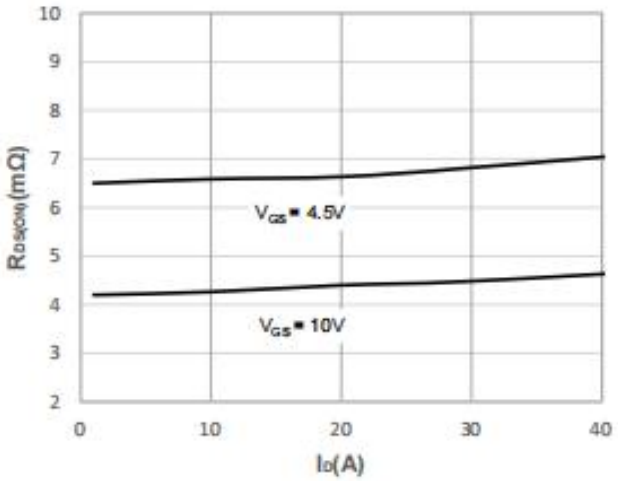


Figure 4: Body Diode Characteristics

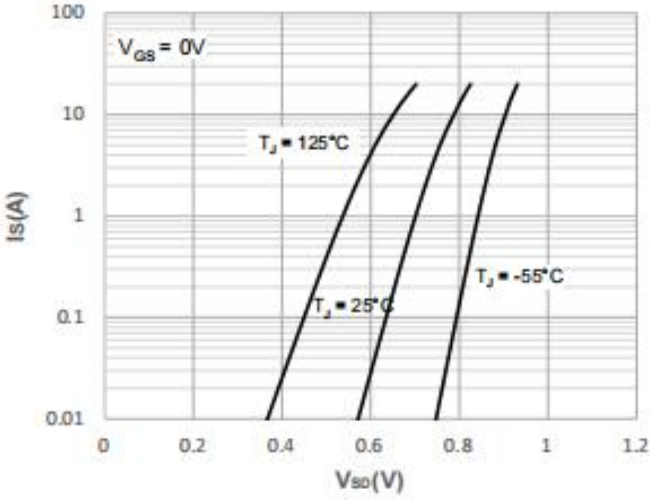


Figure 5: Gate Charge Characteristics

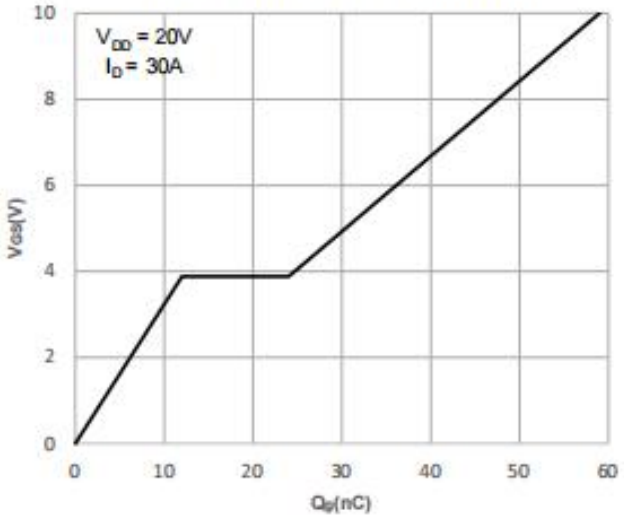


Figure 6: Capacitance Characteristics

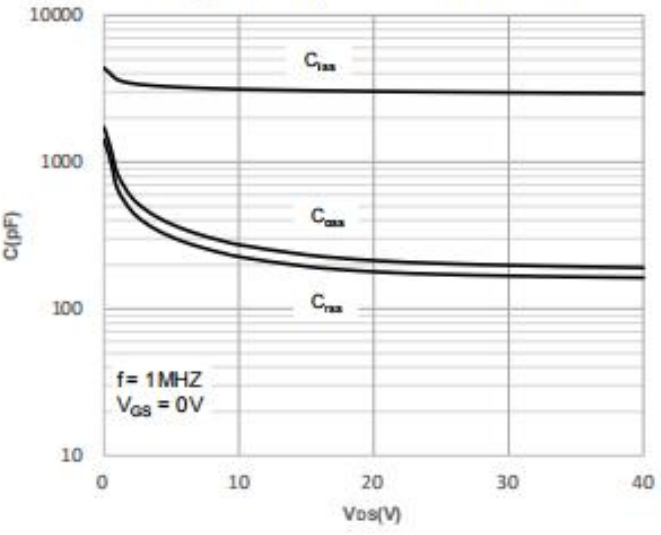


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

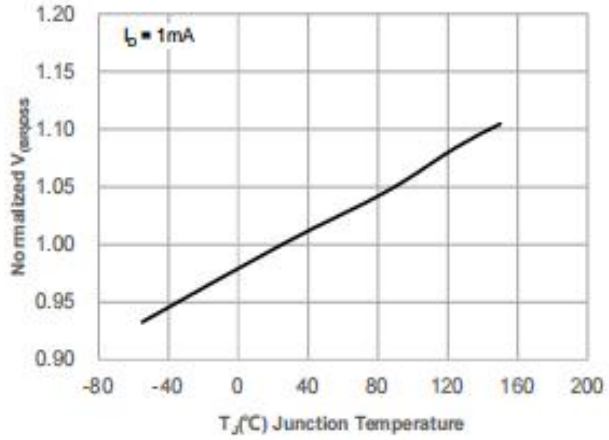


Figure 8: Normalized on Resistance vs. Junction Temperature

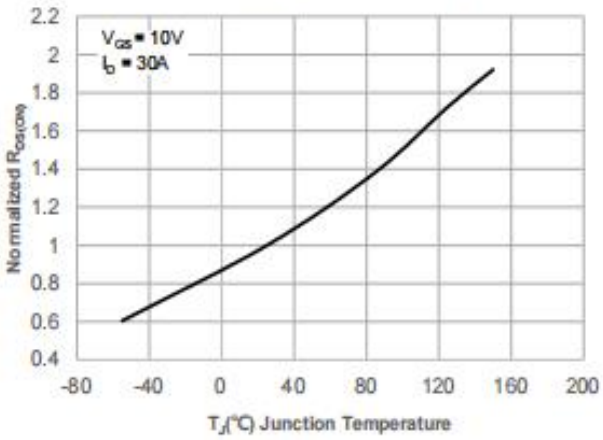


Figure 9: Maximum Safe Operating Area

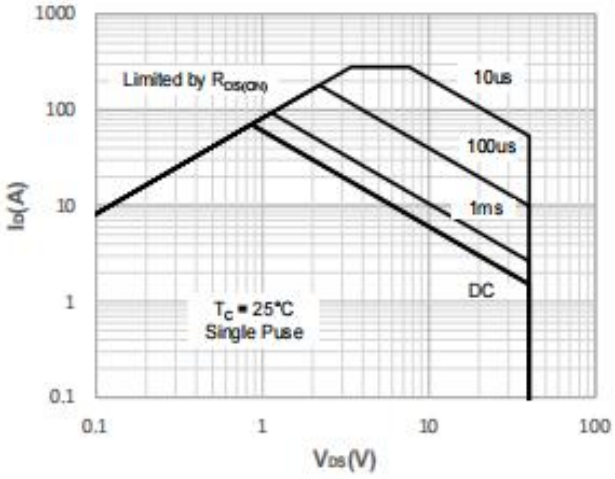


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

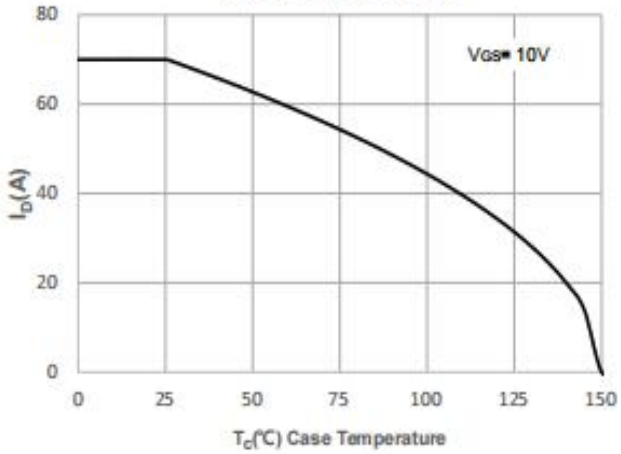


Figure 11: Normalized Maximum Transient Thermal Impedance

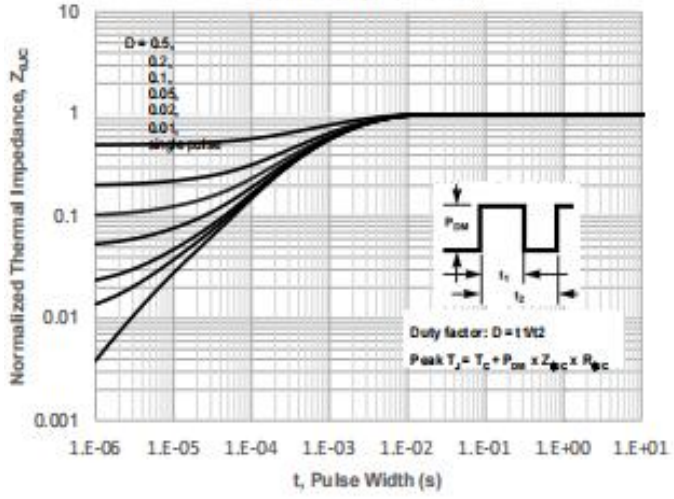
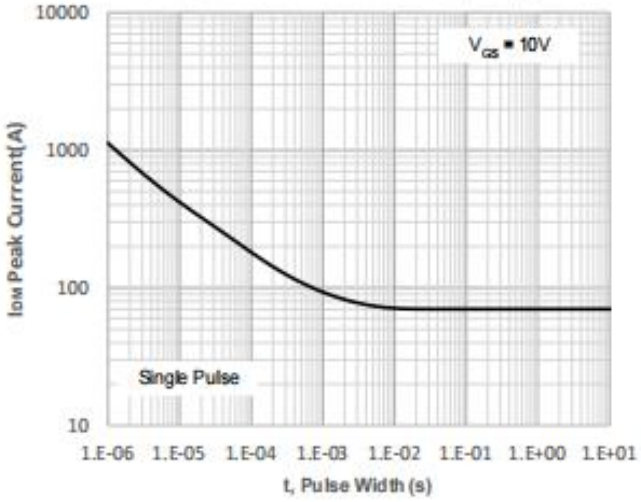


Figure 12: Peak Current Capacity



Test ircuits and Waveforms

Figure A: Gate Charge Test Circuit and Waveform

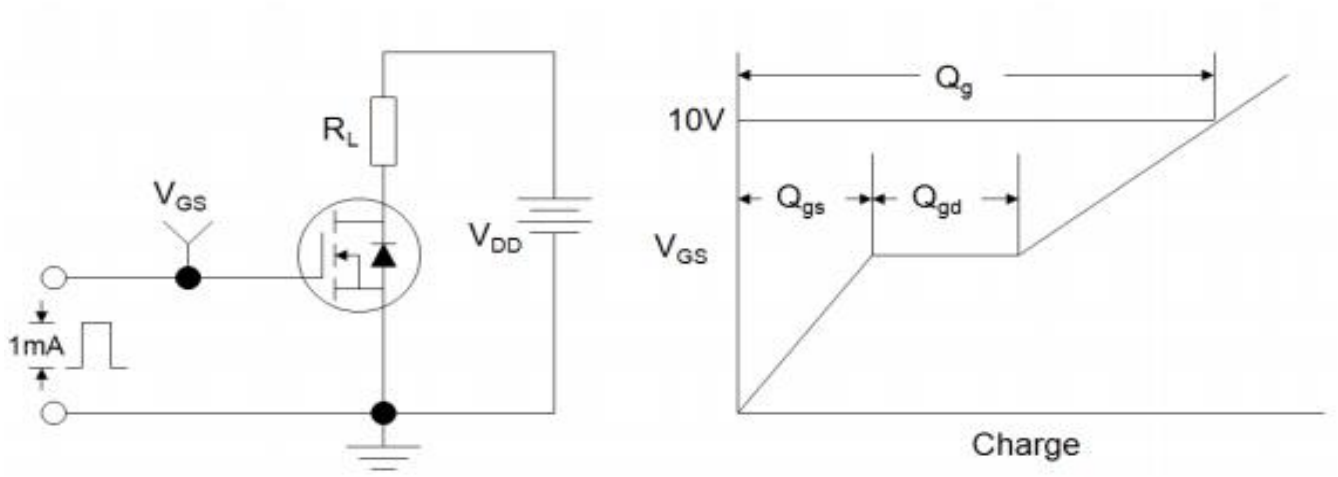


Figure B: Resistive Switching Test Circuit and Waveform

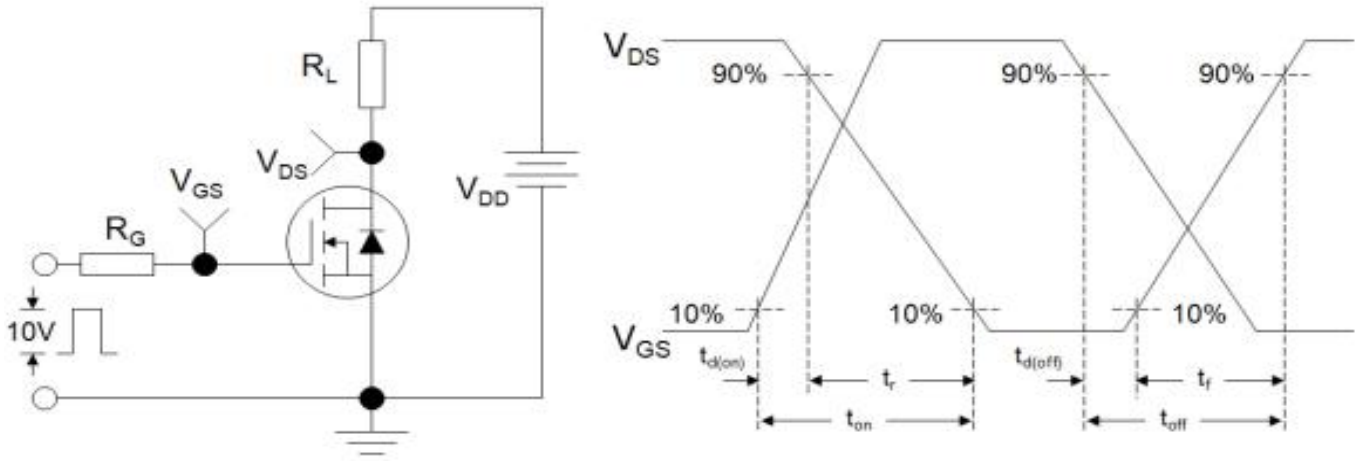
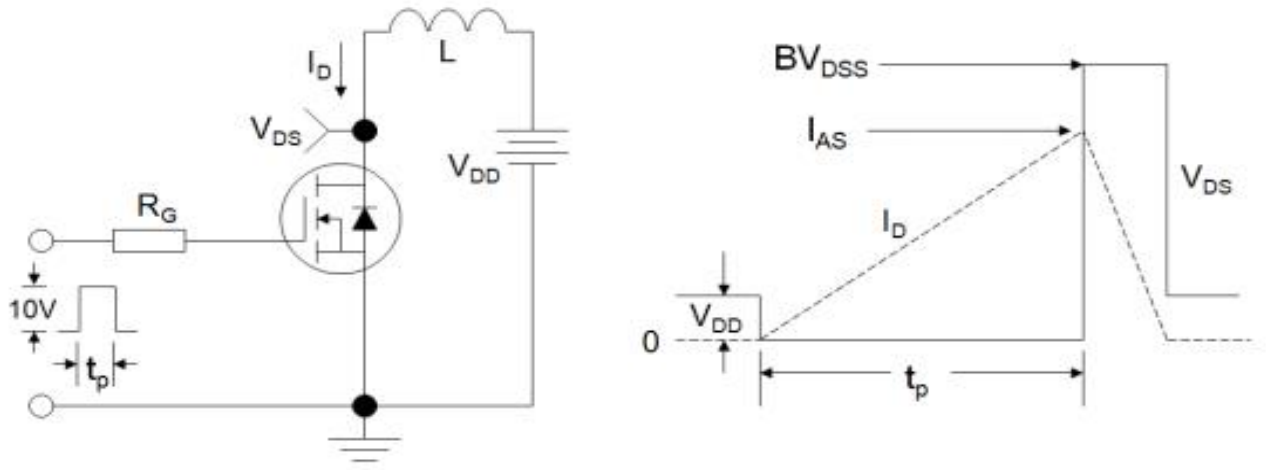
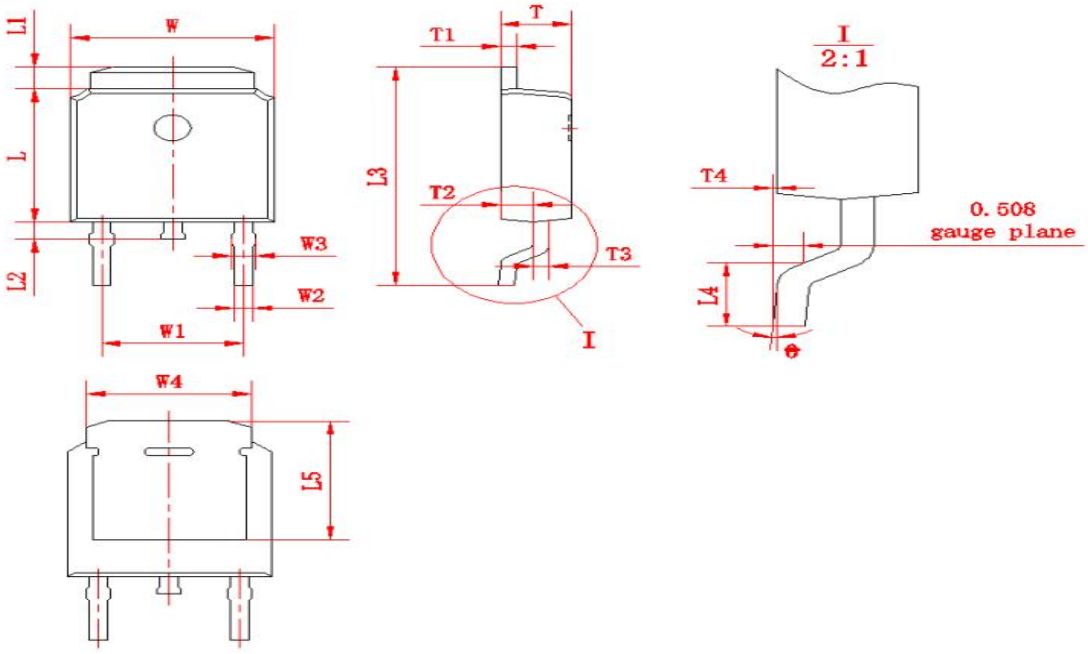


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



Package outline drawing(TO-252 Unit: mm)



符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max
W	6.50	6.70	L1	0.80	1.20	T1	0.48	0.58
W1	(4.572)		L2	0.60	1.00	T2	0.95	1.15
W2	0.6	0.8	L3	9.70	10.30	T3	0.48	0.58
W3	0.68	0.88	L4	1.30	1.70	T4	0.00	0.12
W4	(5.3)		L5	(5.20)		0	0	8
L	6.00	6.20	T	2.20	2.40			

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